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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.120				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.150				
I _D (A)	1.7				
Configuration	Single				
Package	SC-70				

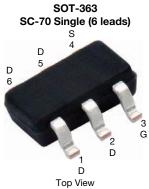
FEATURES

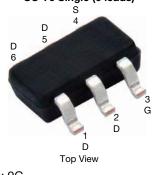
- TrenchFET® power MOSFET
- AEC-Q101 qualified d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT HALOGEN FREE





Marking Code: 9G

G O	
N-Channel MOSFET	o s

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20	V		
$T_C = 25 ^{\circ}\text{C}$			1.7		
Continuous Drain Current ^a	T _C = 125 °C	l _D	1.7		
Continuous Source Current (Diode Conduct	Is	1.7	Α		
Pulsed Drain Current ^b	I _{DM}	6.7			
Single Pulse Avalanche Current	rrent L = 0.1 mH		10		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	5	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	5	3.3	W	
iviaximum Fower Dissipation =	T _C = 125 °C	P_{D}	1.1	VV	
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient PC	CB Mount c	R_{thJA}	125	°C/W
Junction-to-Foot (Drain)	R _{thJF}		45	G/VV

- a. Package limited.
- b. Pulse test; pulse width $\leq 300 \, \mu s$, duty cycle $\leq 2 \, \%$.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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SPECIFICATIONS ($T_C = 25 ^{\circ}C$,	unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							•
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	=	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V _{GS} = 10 V	I _D = 3.8 A	-	0.085	0.120	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V	I _D = 3.8 A, T _J = 125 °C	-	-	0.200	Ω
	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.8 A, T _J = 175 °C	-	-	0.240	
		V _{GS} = 4.5 V	I _D = 3.1 A	-	0.095	0.150	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 1.8 A		-	6	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	275	344	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	34	42	рF
Reverse Transfer Capacitance	C _{rss}			-	13	17	1
Total Gate Charge ^c	Qg			-	4.4	5.5	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 3.8 \text{ A}$	-	0.7	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	1.3	-	
Gate Resistance	Rg		f = 1 MHz	2.1	4.1	6.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	5.8	7.3	
Rise Time ^c	t _r	$V_{DD}=30$ V, $R_{L}=3.9$ Ω $I_{D}\cong3.8$ A, $V_{GEN}=10$ V, $R_{g}=1$ Ω		-	23	29	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	10	13	
Fall Time ^c	t _f			-	30	39	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	11	Α
Forward Voltage	V _{SD}	I _F =	1.8 A, V _{GS} = 0 V	-	0.8	1.2	V

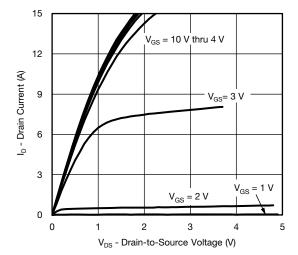
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

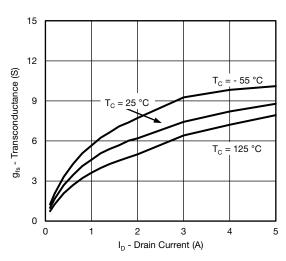
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



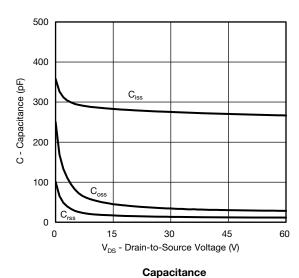
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



Transconductance



15
12
(A) transport of the state of the stat

0

0

2

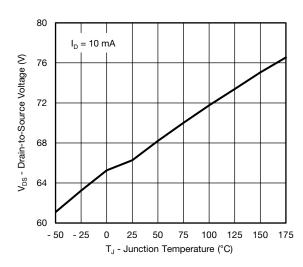
V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

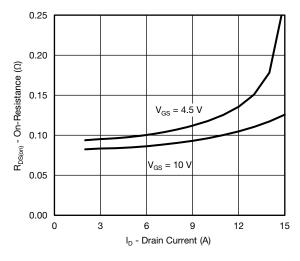
6

8

10



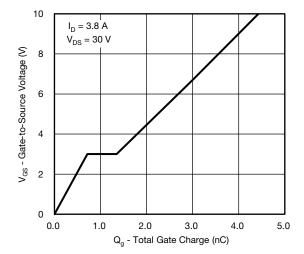
Drain Source Breakdown vs. Junction Temperature



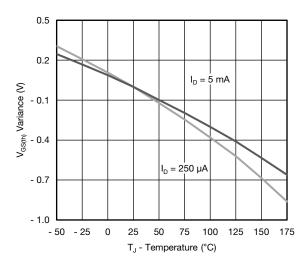
On-Resistance vs. Drain Current



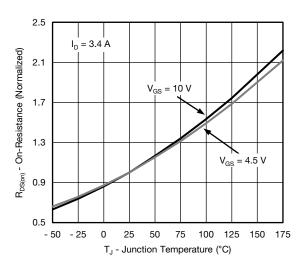
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



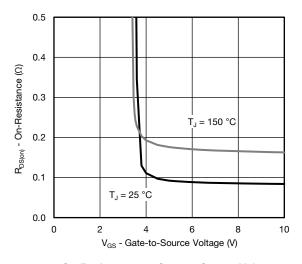
Gate Charge



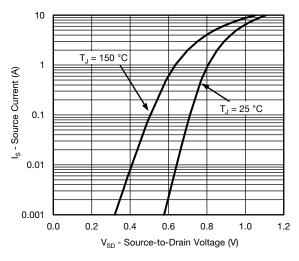
Threshold Voltage



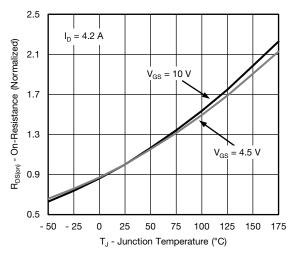
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



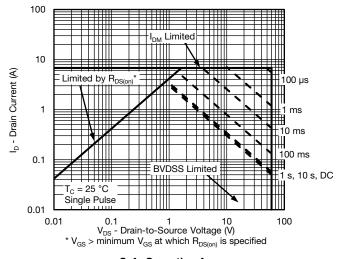
Source Drain Diode Forward Voltage



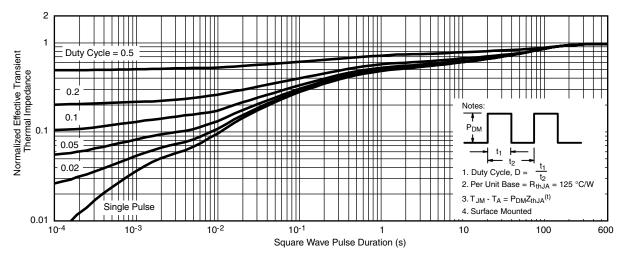
On-Resistance vs. Junction Temperature

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THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



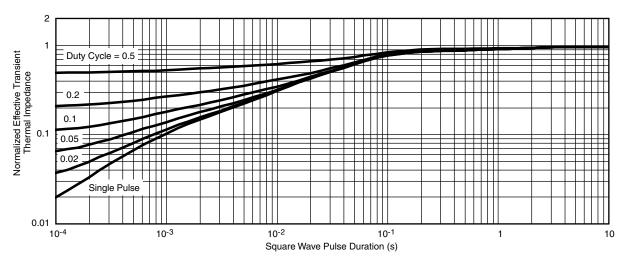
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65884.





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REVISION	HISTORY a	
REVISION	DATE	DESCRIPTION OF CHANGE
В	05-Nov-15	Corrected marking code

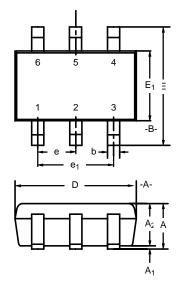
Note

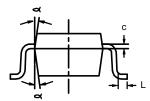
a. As of April 2014





SC-70: 6-LEADS

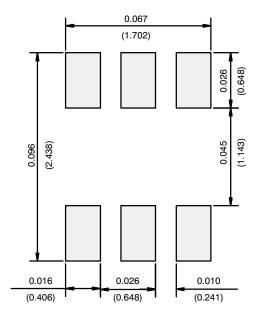




	MIL	LIMET	ERS	INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	_	0.043
A_1	-	-	0.10	-	_	0.004
A ₂	0.80	-	1.00	0.031	_	0.039
b	0.15	-	0.30	0.006	_	0.012
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Ε	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC 0.026BSC					;
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
٦	7°Nom				7°Nom	
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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